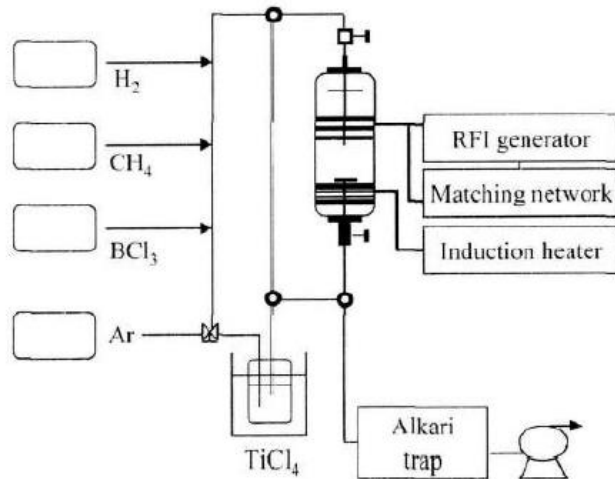


## PECVD법에 의해 증착된 Ti-B-C 코팅막의 보론함량과 증착온도에 따른 물성변화

Ternary Ti-B-C coatings were synthesized on WC-Co and Si wafers substrates by a PECVD technique using a gaseous mixture of  $\text{TiCl}_4$ ,  $\text{BCl}_3$ ,  $\text{CH}_4$ , Ar, and  $\text{H}_2$ . The effects of deposition variables such as substrate temperature, gas ratio,  $R_x = [\text{BCl}_3 / (\text{CH}_4 + \text{BCl}_3)]$  on the microstructure and mechanical properties of Ti-B-C coatings were investigated. From our instrumental analyses, the synthesized Ti-B-C coatings was confirmed to be composites consisting of nanocrystallites TiC, quasi-amorphous  $\text{TiB}_2$ , and amorphous carbon at low boron content, on the contrary, nanocrystallites  $\text{TiB}_2$ , quasi-amorphous TiC, and amorphous carbon at relatively high boron content. The microhardness of the Ti-B-C coatings increased from ~23 GPa of TiC to ~38 GPa of  $\text{Ti}_{0.33}\text{B}_{0.55}\text{C}_{0.11}$  coatings with increasing the boron content. The  $\text{Ti}_{0.33}\text{B}_{0.55}\text{C}_{0.11}$  coatings showed lower average friction coefficient of 0.45, in addition, it showed relatively better wear behavior compared to other binary coatings of  $\text{TiB}_2$  and TiC. The microstruture and microhardness value of Ti-B-C coatings were largely depend on the deposition temperature.



PECVD experimental apparatus.

Typical conditions for Ti-B-C coatings by PECVD

Total flow rate	65 sccm
Working gas ratio [ $\text{TiCl}_4(\text{Ar}) / \text{H}_2$ ]	0.303(30) / 25 sccm
Deposition pressure	133.3 Pa
Deposition time	1 hr
R.F. power	180 Watt
Deposition temperature	370~670°C
$R_x = [\text{BCl}_3 / (\text{BCl}_3 + \text{CH}_4)]$	0~100%

## 실험방법

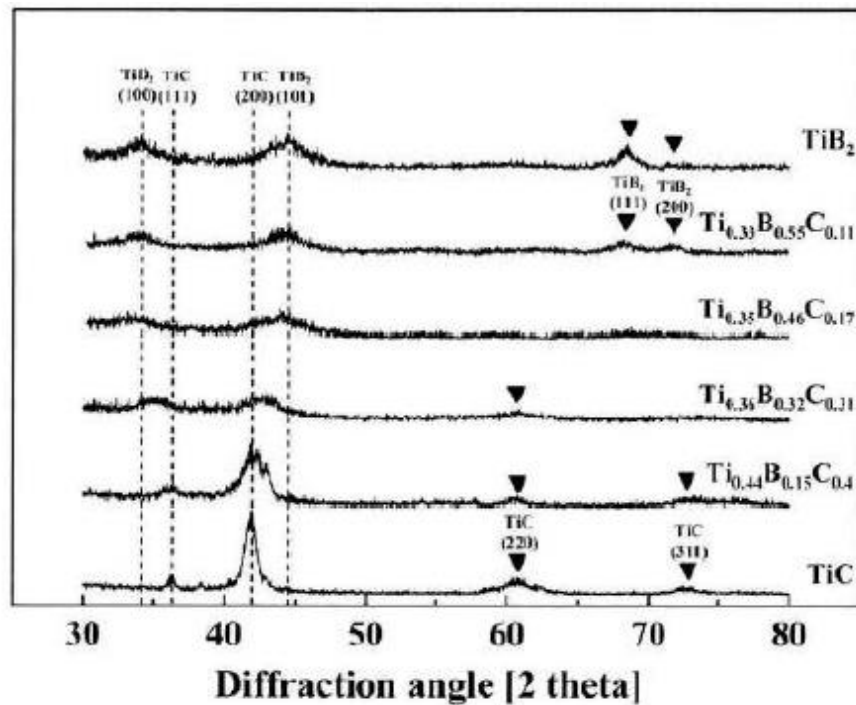
TiBC 박막은 PECVD법에 의해  $\text{TiCl}_4$ ,  $\text{BCl}_3$ ,  $\text{CH}_4$ ,  $\text{H}_2$ , Ar의 반응계에서 WC-Co과 Si기판에 증착 되었다. 증착장치는 반응기체 공급계, 반응로, 저압유지계 및 플라즈마 전원장치로 구성되었다. 챔버는 직경 55mm, 길이 500mm의 석영관, 시편은 유도가열식으로 가열되었다. 저압 유지계는 1 Torr 저압 유지를 위한 Rotary 펌프로 구성되었으며, 전원장치로는 RF 13.56MHz의 matching system을 사용하였다. 반응기체 이송은 유량조절기 와  $\text{TiCl}_4$  bubbler를 이용하였다.

## 결론

PECVD법을 통하여  $\text{TiCl}_4$ ,  $\text{BCl}_3$ ,  $\text{CH}_4$ ,  $\text{H}_2$ , Ar 가스를 이용하여 WC-Co와 Si 기판에 TiBC 박막을 증착 하였다. **B함량**이 적을 때는 박막은 TiC 결정립과 비정질  $\text{TiB}_2$ , 비정질 탄소로 이뤄진 나노-복합체였 으며 반대로 B함량이 많을 때는  $\text{TiB}_2$  결정립과 비정질 TiC와 비정질 탄소로 이루어진 나노복합체 코팅 막으로 확인되었다.

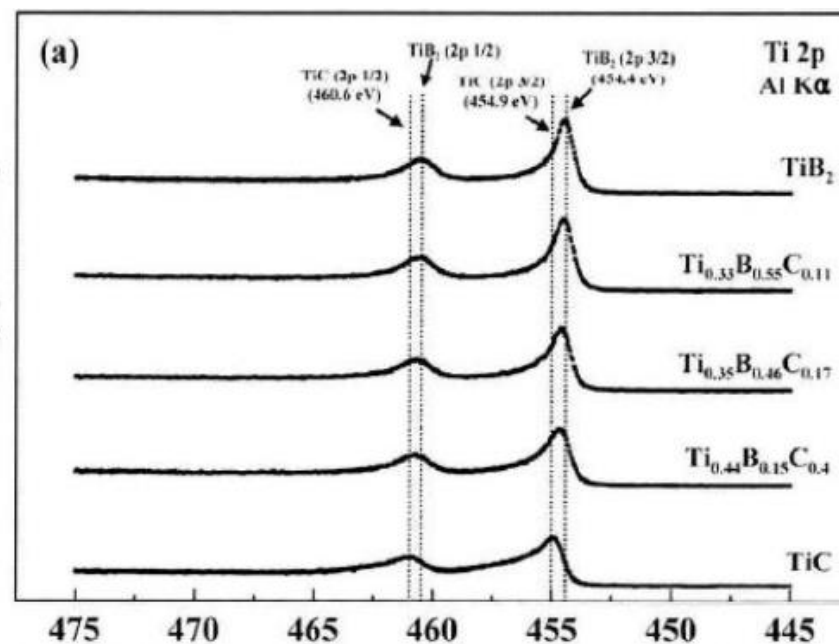
**B함량**이 55 at.%일 때 최고 경도값인 38GPa을 얻을 수 있었으며 이는 2성분 계 코팅막인 TiC에 비 하여 상당히 향상된 수치이다. 또한 평균마찰계수도 TiC,  $\text{TiB}_2$  박막에 비하여 낮은 값(0.45)을 얻을 수 있었다. **증착온도**는 TiBC 막의 결정성과 결정립 크기에 많은 영향을 주었는데 고온에서 합성된 TiBC 막의 결정성은 좋았으나 결정립의 조대화로 인해 경도값이 오히려 감소하는 경향을 보였다.

Intensity [Arb. U.]

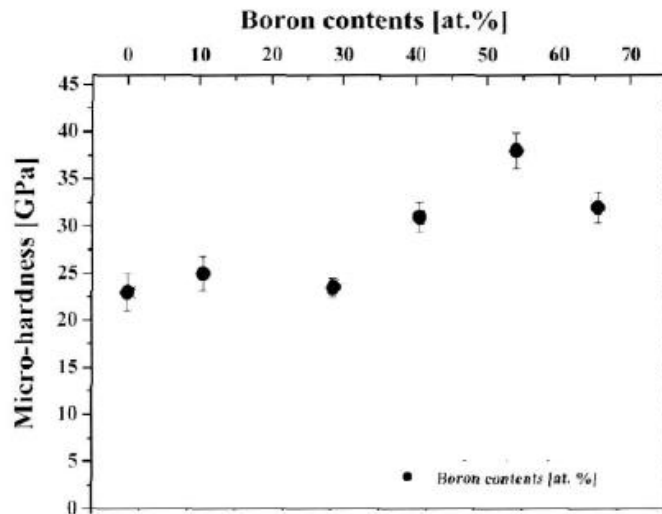


X-ray diffraction patterns of Ti-B-C coatings with various boron contents.

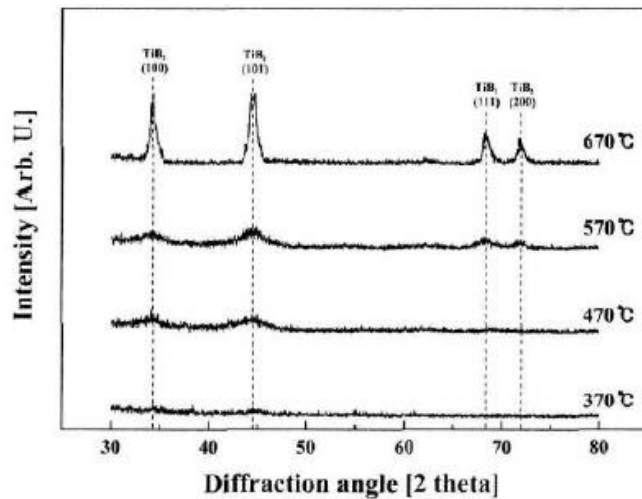
Intensity [Arb. U.]



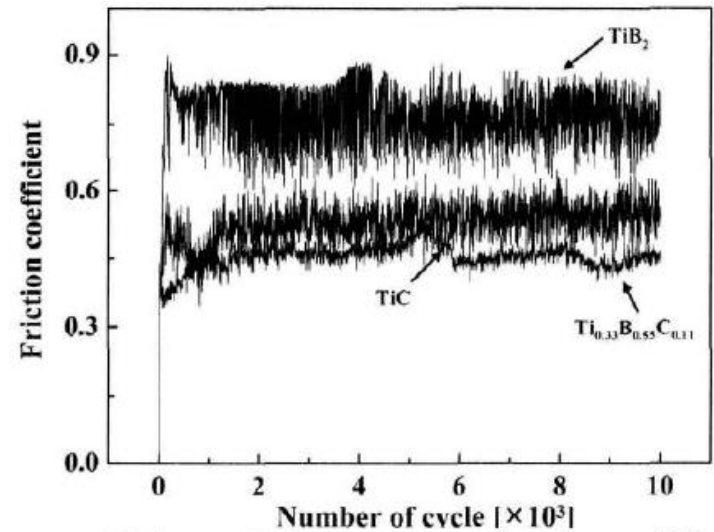
XPS spectra for the Ti 2p at TIBC films



Microhardness values of the Ti-B-C coatings with various boron contents.



X-ray diffraction patterns of Ti-B-C coatings deposited at various deposition temperatures.



Friction coefficients of TiC,  $\text{Ti}_{0.33}\text{B}_{0.55}\text{C}_{0.11}$ , and  $\text{TiB}_2$  coatings.

